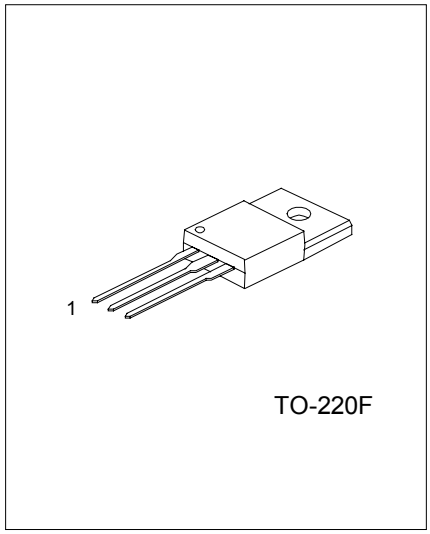
TRIACS

DESCRIPTION

Glass passivated , sensitive gate triacs in a full pack plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.



1:MT1 2:MT2 3:GATE

SYMBOL

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive Peak Off-State Voltage UT137FE-5 UT137FE-6 UT137FE-8	V_{DRM}	 500* 600* 800	V
RMS On-state Current Full sine wave; $T_{hs} \leqslant 73°C$	$I_{T(RMS)}$	8	A
Non-Repetitive Peak. On-State Current Full sine wave,T_j=125°C prior to surge,with reapplied,V_{DRM}(max) t=20ms t=16.7ms	I_{TSM}	 55 60	A
I^2t For Fusing (t=10ms)	I^2t	15	A^2s
Repetitive Rate of Rise of On-state Current after Triggering I_{TM}=12A;I_G=0.2A,dI_G/dt=0.2A/μs T2+ G+ T2+ G- T2- G- T2- G+	dI_T/dt	 50 50 50 10	A/μs
Peak Gate Voltage	V_{GM}	5	V
Peak Gate Current	I_{GM}	2	A
Peak Gate Power	P_{GM}	5	W
Average Gate Power (Over any 20ms period)	$P_{G(AV)}$	0.5	W
Operating Junction Temperature	Tj	125	°C
Storage Temperature	Tstg	-40~150	°C

*Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6A/μs.

ISOLATION LINITING VALUE & CHARACTERISTIC(T_{hs}=25°C,unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Repetitive paek voltage form all three terminals to external heatsink (R.H.≦65%,clean and dustfree)	Visol			1500	V
Capacitance from MT2 to external heatsink (f=1MHz)	Cisol		12		pF

THERMAL RESISTANCES

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Thermal Resistance Junction to heatsink (full or half cycle) with heatsink compound without heatsink compound	Rth j-hs			4.5 6.5	K/W
Thermal Resistance Junction to Ambient (In free air)	Rth j-a		55		K/W

STATIC CHARACTERISTICS (T_j=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate Trigger Current	I_{GT}	V_D=12V, I_T=0.1A				
		T2+ G+		2.5	10	mA
		T2+ G-		4.0	10	
		T2- G-		5.0	10	
		T2- G+		11	25	
Latching Current	I_L	V_D=12V, I_{GT}=0.1A				
		T2+ G+		3.0	25	mA
		T2+ G-		14	35	
		T2- G-		3.0	25	
		T2- G+		4.0	35	
Holding Current	I_H	V_D=12V, I_{GT}=0.1A		2.5	20	mA
On-State Voltage	V_T	I_T=10A		1.3	1.65	V
Gate Trigger Voltage	V_{GT}	V_D=12V, I_T=0.1A		0.7	1.5	V
		V_D=400V, I_T=0.1A, Tj=125°C	0.25	0.4		V
Off-state Leakage Current	I_D	V_D=$V_{DRM(max)}$, Tj=125°C		0.1	0.5	mA

DYNAMIC CHARACTERISTICS (T_j=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Critical Rate of Rise of off-state Voltage	dV_D/dt	V_{DM}=67% $V_{DRM(max)}$, Tj=125°C Exponential waveform,Gate open circuit		50		V/μs
Gate Controlled Turn-on Time	tgt	I_{TM}=12A,V_D=$V_{DRM(max)}$,I_G=0.1A, dI_G/dt=5A/μs		2		μs

TYPICAL CHARACTERISTICS

Figure 1.Maximum on -state Dissipation.Ptot vs RMS On-state Current,$I_{T(RMS)}$,Where α =Conduction Angle.

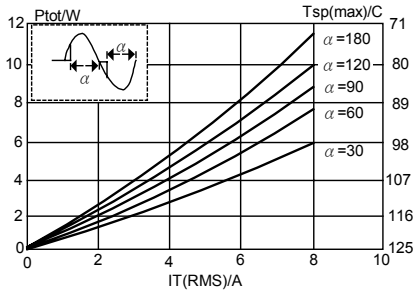


Figure 4.Maximum Permissible RMS Current $I_{T(RMS)}$ vs Heatsink Temperature T_{hs}

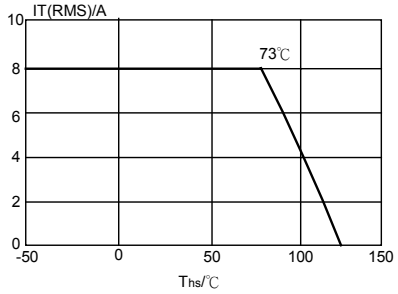


Figure 2. Maximum Permissible Non-repetitive Peak On-state Current I_{TSM},vs Pulse Width t_p,for Sinusoidal Currents,$t_p \leqq 20ms$

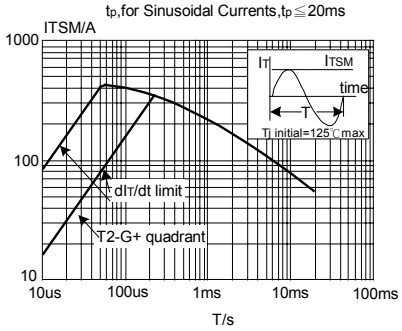


Figure 5.Maximum Permissible Repetitive RMS on-state Current $I_{T(RMS)}$,vs Surge Duration,for Sinusoidal Currents,f=50Hz;$T_{hs} \leqq 73℃$

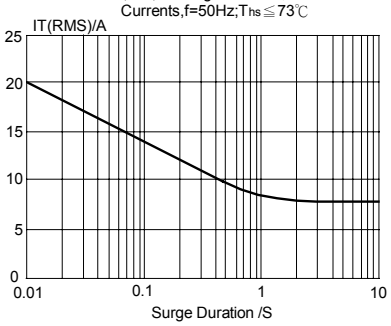


Figure 3 .Maximum Permissible Non-Repetitive peak on-state Current I_{TSM},vs Number of Cycles, for Sinusoidal Currents,f=50Hz

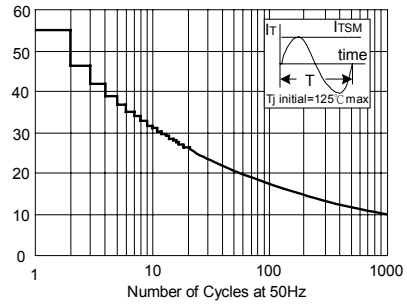


Figure 6.Normalised Gate Trigger Voltage $V_{GT}(Tj)$/ $V_{GT}(25℃)$,vs Junction Temperature Tj

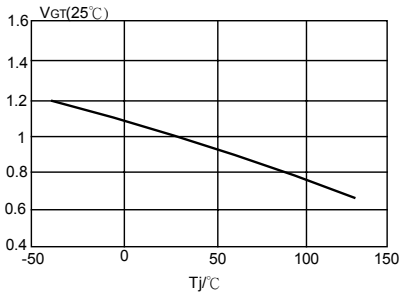


Figure 7.Normalised Gate Trigger Current
$I_{GT}(Tj)/I_{GT}(25℃)$,vs Junction Temperature Tj

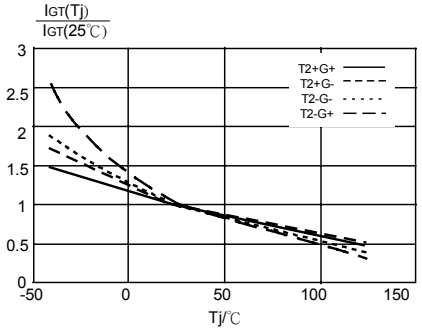


Figure 8.Normalised Latching Current
$I_L(Tj)/I_L(25℃)$,vs Junction Temperature Tj

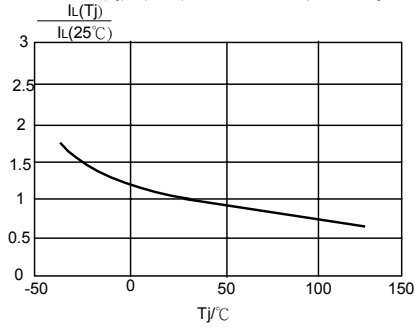


Figure 9.Normalised Holding Current
$I_H(Tj)/I_H(25℃)$,vs Junction Temperature Tj

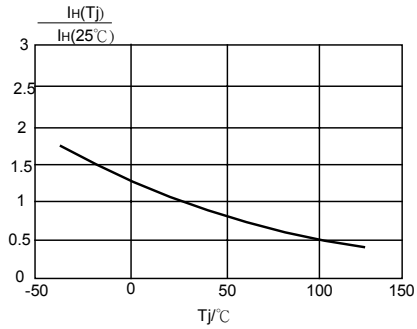


Figure 10.Typical and Maximum
On-state Characteristic

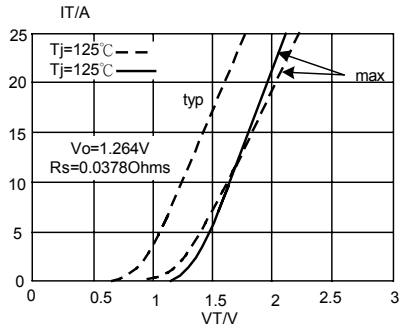


Figure 11.Transient Thermal Impedance
Zth j-hs,vs Pulse Width tp

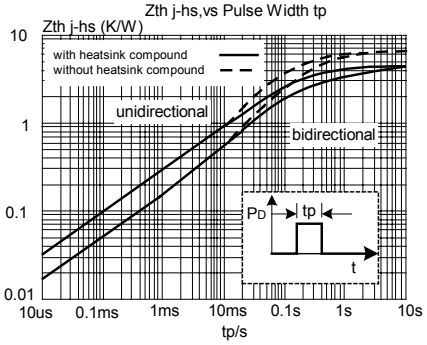


Figure 12.Typical ,critical rate of rise of off-state
voltage,dV_D/dt versus junction temperature Tj